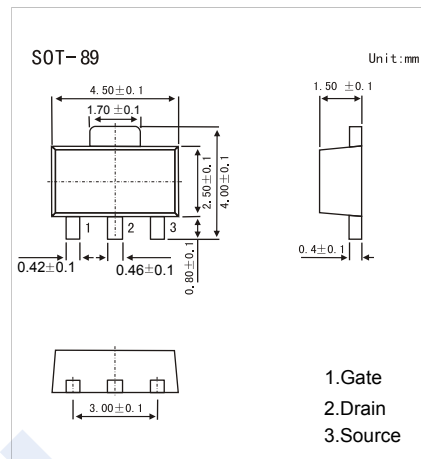
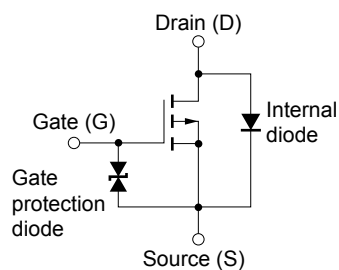


P-Channel MOSFET

2SJ356

■ Features

- $V_{DS} (V) \approx -60V$
- $I_D \approx -2 A (V_{GS} \approx -10V)$
- $R_{DS(ON)} < 0.5 \Omega (V_{GS} \approx -10V)$
- $R_{DS(ON)} < 0.95 \Omega (V_{GS} \approx -4V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	-20, +10	
Continuous Drain Current	I_D	-2	A
Pulsed Drain Current (Note.1)	I_{DM}	-4	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10 \text{ ms}$, duty cycle $\leq 1\%$

P-Channel MOSFET

2SJ356

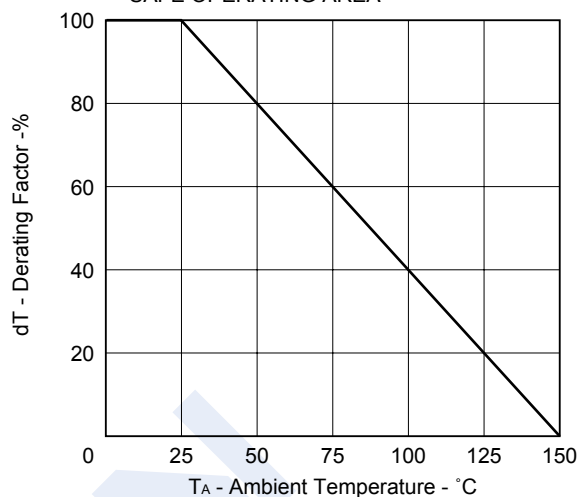
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D = -250\ \mu\text{A}$, $V_{GS} = 0\text{V}$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}$, $V_{GS} = 0\text{V}$			-10	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 16\text{V}$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10\text{V}$, $I_D = -1\text{mA}$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{V}$, $I_D = -1\text{A}$			0.5	Ω
		$V_{GS} = -4\text{V}$, $I_D = -1\text{A}$			0.95	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}$, $I_D = -1\text{A}$	1			S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		270		pF
Output Capacitance	C_{oss}			145		
Reverse Transfer Capacitance	C_{rss}			55		
Gate Input Charge	Q_G	$V_{GS} = -10\text{V}$, $V_{DS} = -48\text{V}$, $I_D = -2\text{A}$, $I_G = -2\text{mA}$		11.6		nC
Gate to Source Charge	Q_{GS}			1		
Gate to Drain Charge	Q_{GD}			3.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)} = -10\text{V}$, $I_D = -1\text{A}$, $R_L = 25\ \Omega$, $R_G = 10\ \Omega$, $V_{DD} = -25\text{V}$		4.3		ns
Turn-On Rise Time	t_r			21		
Turn-Off Delay Time	$t_{d(off)}$			115		
Turn-Off Fall Time	t_f			75		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2\text{A}$, $dI/dt = 50\text{A}/\mu\text{s}$		82		nC
Internal Diode Reverse Recovery Ch	Q_{rr}			94		

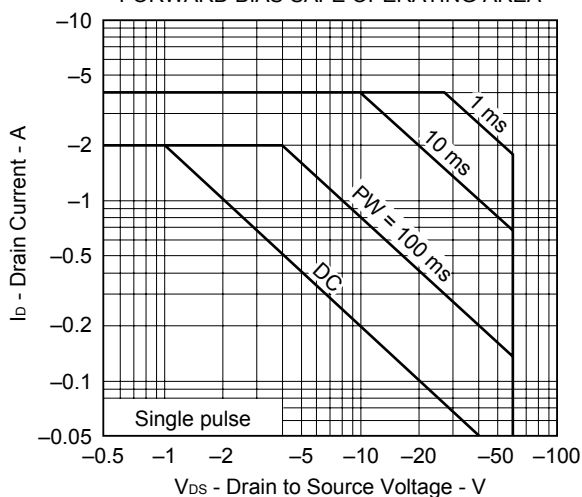
■ Marking

Marking	PR
---------	----

■ Typical Characteristics

DERATING FACTOR OF FORWARD BIAS
SAFE OPERATING AREA

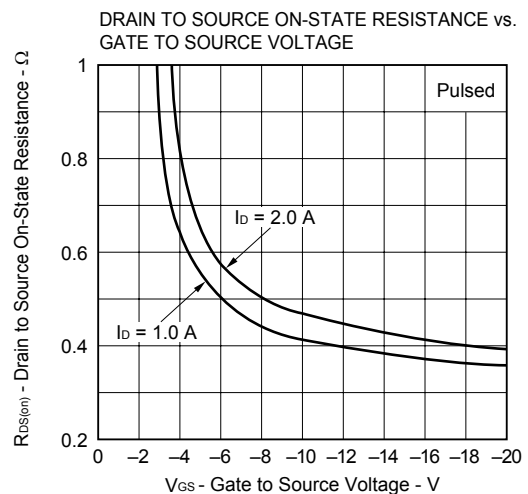
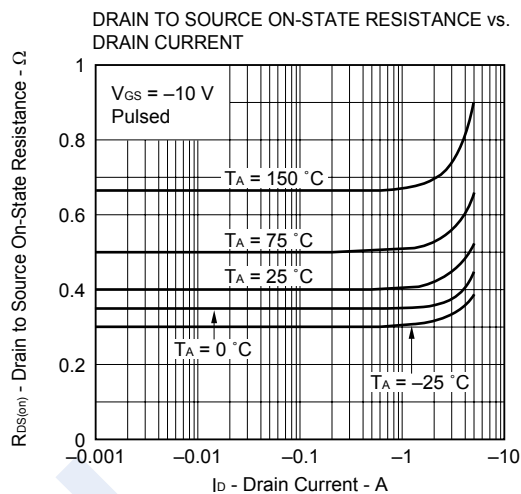
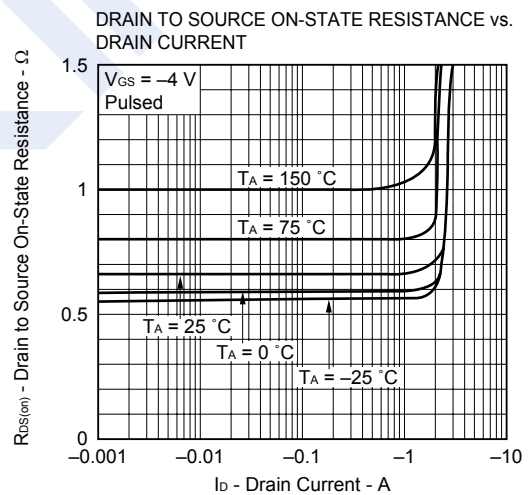
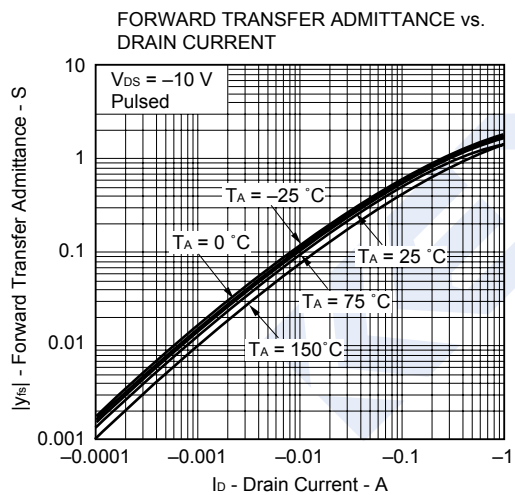
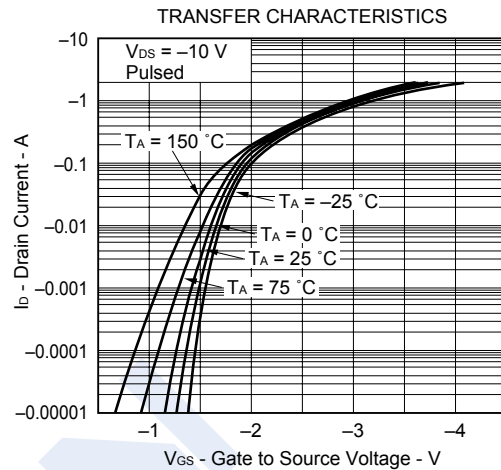
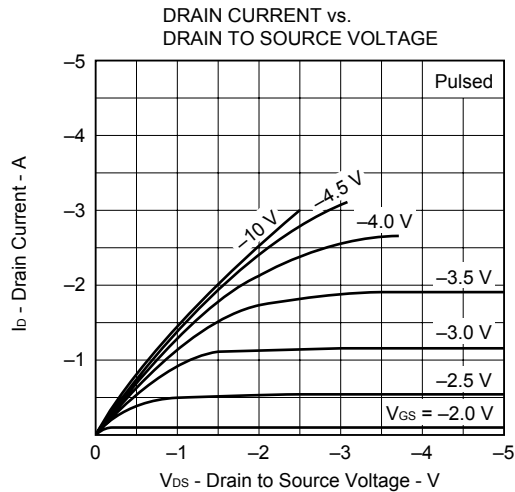
FORWARD BIAS SAFE OPERATING AREA



P-Channel MOSFET

2SJ356

■ Typical Characteristics



P-Channel MOSFET

2SJ356

■ Typical Characteristics

